

claim 10  
a first passivation layer formed on said adhesion layer, said first passivation layer and said adhesion layer including at least one common chemical element.

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b6  
19. (Amended) The integrated circuit of claim 17 wherein said oxide layer includes silicon dioxide (SiO<sub>2</sub>).

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b7  
23. (Amended) An integrated circuit comprising in a three layer stack:  
a silicon dioxide insulating layer;  
a silicon oxynitride adhesion layer formed on said silicon dioxide insulating layer;  
and  
a silicon nitride hard passivation layer formed on said silicon oxynitride adhesion layer.

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